L Number	Hits	Search Text	DB	Time stamp
1	1	"20030008505"	US-PGPUB	2003/08/20 17:26
2	2	(silicide same (self near2 grow\$3)) same silicon	USPAT;	2003/08/20 17:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	1093	(silicide same grow\$3) same (silicon same etch\$3)	USPAT;	2003/08/20 17:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	0	((silicide same grow\$3) same (silicon same etch\$3)) same	USPAT;	2003/08/20 17:32
		(nano near wire)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
5	0	(silicide same grow\$3) same (nano near wire)	USPAT;	2003/08/20 17:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
6	14		IBM_TDB	2002/00/00 47-22
6	14	grow\$3 same (nano near wire)	USPAT; US-PGPUB;	2003/08/20 17:32
			EPO; JPO; DERWENT;	
			IBM_TDB	
7	5920	silicide same silicon	USPAT;	2003/08/20 17:57
1	0020	Silicide Suffic Silicon	US-PGPUB;	2003/00/20 17.37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	96	(silicide same silicon) same ((anisotropic\$4 near etch\$3) same	USPAT;	2003/08/20 20:00
		silicon)	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	0	(((silicide same silicon) same ((anisotropic\$4 near etch\$3)	USPAT;	2003/08/20 18:00
		same silicon)) and @pd<20011113) and (nano near wire)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(/ 27)	IBM_TDB	
9	77	((silicide same silicon) same ((anisotropic\$4 near etch\$3)	USPAT;	2003/08/20 18:00
		same silicon)) and @pd<20011113	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
11	17532	(anisotropic\$4 near etch\$3) same silicon	IBM_TDB USPAT;	2003/08/20 18:03
1	17002	Compositopiogramical etenigo) same sincon	US-PGPUB;	2003/00/20 10:03
	· ·		EPO; JPO;	
			DERWENT;	· ·
			IBM TDB	
12	59	((anisotropic\$4 near etch\$3) same silicon) same (mask\$3	USPAT;	2003/08/20 18:03
		near5 silicide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1 1			IBM_TDB	
13	42	(((anisotropic\$4 near etch\$3) same silicon) same (mask\$3	USPAT;	2003/08/20 18:43
		near5 silicide)) and @pd<20011113	US-PGPUB;	
			EPO; JPO;	
]			DERWENT;	
44		(none near wire) come ellipse	IBM_TDB	0000/00/00 10 55
14	14	(nano near wire) same silicon	USPAT;	2003/08/20 19:38
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	l

15	0	(nano near wire or nano near structure or nano near pattern)	USPAT;	2003/08/20 19:41
		same ((epitaxial\$2 near grow\$3) same silicon)	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
16	1	(nano near wire or nano near structure or nano near pattern)	USPAT;	2003/08/20 19:45
10	'	same (epitaxial\$2 near grow\$3)	US-PGPUB;	2003/00/20 19.43
		Same (epitaxiai#2 near grow#5)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
17	154062	(etch\$3 or pattern\$3) same silicon	USPAT;	2003/08/20 19:45
!			US-PGPUB;	
1			EPO; JPO;	
l			DERWENT;	
			IBM_TDB	
18	1548	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:46
		silicide)	US-PGPUB;	
			EPO; JPO;	
Ì			DERWENT;	
10		(((stah\$2 ar nottorn\$2) same silican) same (mask\$2 with	IBM_TDB	2002/09/20 40:47
19	0	(((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) same nano	USPAT; US-PGPUB;	2003/08/20 19:47
		Sincide)) Same nano	EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
20	1213	(((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:54
		silicide)) and ((nano near wire) or (nano structure))	US-PGPUB;	2000/00/20 10:07
		((,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
21	936	((((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:48
		silicide)) and ((nano near wire) or (nano structure))) and	US-PGPUB;	,
1		insulat\$3	EPO; JPO;	
			DERWENT;	
22	0	(((((atab\$2 or nattorn\$2) come cilican) come (mack\$2 with	IBM_TDB	2002/08/20 40-50
22	"	(((((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano structure))) and	USPAT; US-PGPUB;	2003/08/20 19:50
		insulat\$3) and @pd<2001626	EPO; JPO;	
		modulação, and wpa 1200 1020	DERWENT;	
			IBM_TDB	
23	532	(((((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:54
		silicide)) and ((nano near wire) or (nano structure))) and	US-PGPUB;	
		insulat\$3) and @pd<20010626	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
24	1	((((((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:52
		silicide)) and ((nano near wire) or (nano structure))) and	US-PGPUB;	
		insulat\$3) and @pd<20010626) and 216/41.ccls.	EPO; JPO;	
			DERWENT;	
25	0	(((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:56
		(((etchas of patternas) same shicon) same (maskas with silicide)) and ((nano near wire) or (nano near structure))	US-PGPUB;	2000/00/20 19.00
		The state of the s	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	0	(((etch\$3 or pattern\$3) same silicon) same (mask\$3 with	USPAT;	2003/08/20 19:56
		silicide)) and ((nano near wire) or (nano near structure))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
27	1-	(/ailiaida anno ailiann) anno (/ailiaida anno ailiann)	IBM_TDB	2002/00/02 22 22
27	45	((silicide same silicon) same ((anisotropic\$4 near etch\$3)	USPAT;	2003/08/20 20:00
		same silicon)) and (insulat\$3)	US-PGPUB; EPO; JPO;	1
			DERWENT;	ļ.
			IBM_TDB	
L			1.51.55	1